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### VS-ETX1506S-M3, VS-ETX1506-1-M3

Vishay Semiconductors

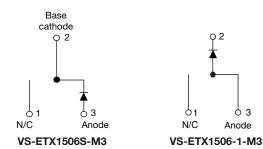
### Hyperfast Rectifier, 15 A FRED Pt<sup>®</sup>





**TO-262AA** 

TO-263AB (D<sup>2</sup>PAK)



PRODUCT SUMMARY	
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA
I <sub>F(AV)</sub>	15 A
V <sub>R</sub>	600 V
V <sub>F</sub> at I <sub>F</sub>	1.55 V
t <sub>rr</sub> (typ.)	18 ns
T <sub>J</sub> max.	175 °C
Diode variation	Single die

### FEATURES

- Hyperfast recovery time, extremely low Qrr
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recover time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 127 °C	15	٨		
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	120	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-			
E	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	2.5	3.4	V		
Forward voltage		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.55	2			
		$V_R = V_R$ rated	-	0.02	36			
Reverse leakage current	I <sub>R</sub>	$T_J = 150 \ ^{\circ}C, V_R = V_R$ rated	-	40	250	μA		
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	12	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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Document Number: 93594

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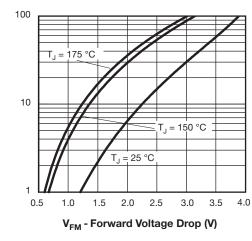


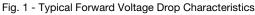
**Vishay Semiconductors** 

DYNAMIC RECOVERY CH	IARACTER	<b>RISTICS</b> ( $T_J = 25$	5 °C unless otherw	ise speci	fied)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 1$	00 A/µs, V <sub>R</sub> = 30 V	-	17	23	
Bowerse receiver time	+	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/µs, V <sub>R</sub> = 30 V	-	18	30	ns
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	20	-	115
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 390 V	-	45	-	
Pool room ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.7	-	А
Peak recovery current		T <sub>J</sub> = 125 °C		-	5.5	-	A
	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	26	-	nC
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	130	-	nc
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 15 A	-	32	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 800 A/µs	-	17	-	А
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	290	-	nC

THERMAL - MECHANICA	THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.3	1.51	°C/W			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	70				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-				
Maight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style D <sup>2</sup> PAK	ETX1506S						
Marking device		Case style TO-262		ETX1	506-1				







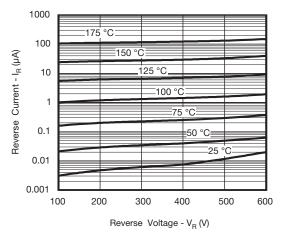


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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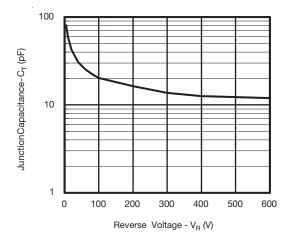


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

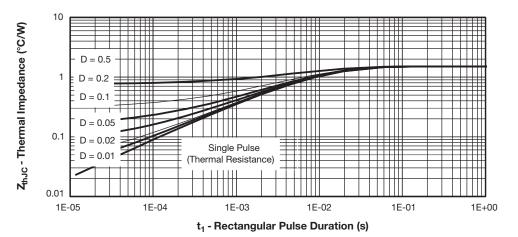
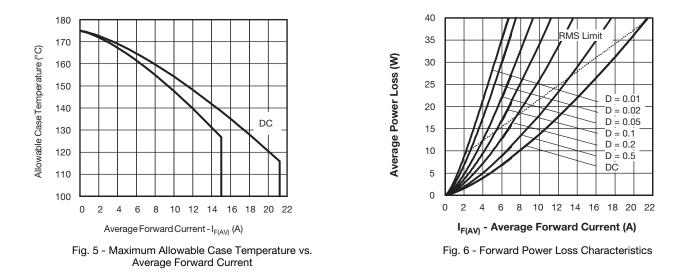


Fig. 4 - Max. Thermal Impedance Z<sub>thJC</sub> Characteristics



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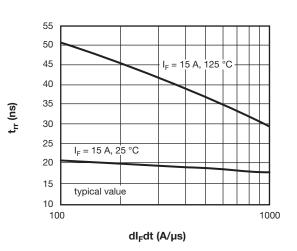
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### VS-ETX1506S-M3, VS-ETX1506-1-M3





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Fig. 7 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

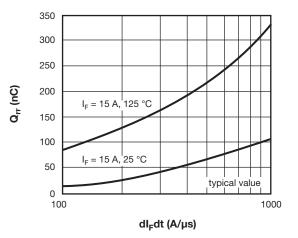


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

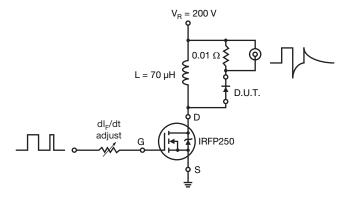
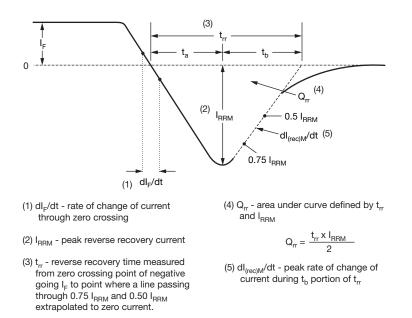
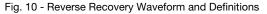


Fig. 9 - Reverse Recovery Parameter Test Circuit







## VS-ETX1506S-M3, VS-ETX1506-1-M3

### Vishay Semiconductors

#### **ORDERING INFORMATION TABLE**

Device code	VS-	E	т	x	15	06	S	TRL	-M3
		2	3	4	5	6	7	8	9
	<ol> <li>Vishay Semiconductors product</li> <li>Circuit configuration</li> </ol>								
	3 -	E =	single o TO-220	diode					
	4 -	- X =	hyperfa	st recov	ery time	9			
	5 -			le (15 =					
	6 · 7 ·		= D <sup>2</sup> PAI	le (06 = K	000 V)				
		• -1	= TO-20	62					
	8	• No	one = tu	be (50 p	oieces)				
	- • TRL = tape and reel (left oriented, for D <sup>2</sup> PAK package)								
		• TF	RR = tap	e and re	eel (righ	t oriente	ed, for [	) <sup>2</sup> PAK	package
	9	- M3	= halog	gen-free	, RoHS-	complia	ant and	termina	ations le

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-ETX1506S-M3	50	1000	Antistatic plastic tube				
VS-ETX1506-1-M3	50	1000	Antistatic plastic tube				
VS-ETX1506STRR-M3	800	800	13" diameter reel				
VS-ETX1506STRL-M3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95046				
	TO-262AA	www.vishay.com/doc?95419				
Davt marking information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	TO-263AB (D <sup>2</sup> PAK)	www.vishay.com/doc?95032				

### **Outline Dimensions**



D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches

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SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 08-Jul-15

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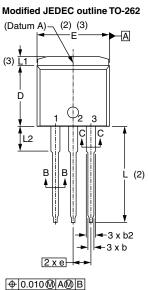


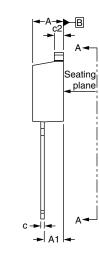
### **Outline Dimensions**

**Vishay Semiconductors** 

**TO-262** 

#### **DIMENSIONS** in millimeters and inches

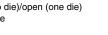


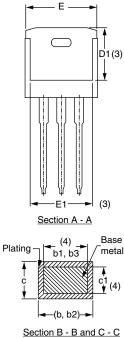


Lead assignments



**Diodes** 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode





Scale: None

SYMBOL	MILLIM	ETERS	INC	NOTEO	
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.10	0 BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

#### Notes

Revision: 04-Oct-10

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

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